

Kunio Okimura

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6415688/publications.pdf>

Version: 2024-02-01

50
papers

823
citations

516710

16
h-index

501196

28
g-index

50
all docs

50
docs citations

50
times ranked

942
citing authors

#	ARTICLE	IF	CITATIONS
1	Dynamic Quarter-Wave Metasurface for Efficient Helicity Inversion of Polarization Beyond the Single-Layer Conversion Limit. <i>Advanced Optical Materials</i> , 2022, 10, 2101615.	7.3	9
2	Dynamic inversion of planar-chiral response of terahertz metasurface based on critical transition of checkerboard structures. <i>Nanophotonics</i> , 2022, 11, 2057-2064.	6.0	4
3	VO ₂ films on flexible thin polyimide films: Fabrication and characterization of electrical and optical properties in insulator-metal transition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2022, 40, .	2.1	1
4	Electrochemical Probing of H ₂ O ₂ Using TiO ₂ -ZrO ₂ -HfO ₂ Modified Glassy Carbon Electrode: A Promoted Sacrificial Behavior of Hf ⁴⁺ ions. <i>Water, Air, and Soil Pollution</i> , 2021, 232, 1.	2.4	2
5	Approaching ultrathin VO ₂ films on sapphire (001) substrates by biased reactive sputtering: Characteristic morphology and its effect on the infrared-light switching. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021, 39, .	2.1	5
6	Broadband operation of active terahertz quarter-wave plate achieved with vanadium-dioxide-based metasurface switchable by current injection. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	14
7	Stress-Induced In Situ Modification of Transition Temperature in VO ₂ Films Capped by Chalcogenide. <i>Materials</i> , 2020, 13, 5541.	2.9	1
8	Coupled oscillations of VO ₂ -based layered structures: Experiment and simulation approach. <i>Journal of Applied Physics</i> , 2020, 127, .	2.5	12
9	Simultaneous realization of infrared-light switching and high visible-light transmittance in extremely thin VO ₂ films grown on ZnO-nanorods buffered glasses. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020, 38, .	2.1	3
10	Persistent M ₂ phase in strongly strained (011)-oriented grains in VO ₂ films grown on sapphire (001) in reactive sputtering. <i>Journal of Applied Physics</i> , 2019, 125, .	2.5	7
11	Reconfigurable Terahertz Quarter-Wave Plate for Helicity Switching Based on Babinet Inversion of an Anisotropic Checkerboard Metasurface. <i>Physical Review Applied</i> , 2019, 11, .	3.8	22
12	Infrared-light switching in highly oriented VO ₂ films on ZnO-buffered glasses with controlled phase transition temperatures. <i>Solar Energy Materials and Solar Cells</i> , 2019, 191, 9-14.	6.2	17
13	Low-temperature growth of VO ₂ films on transparent ZnO/glass and Al-doped ZnO/glass and their optical transition properties. <i>Thin Solid Films</i> , 2018, 651, 91-96.	1.8	14
14	Activities of Sputtering and Plasma Process (SP) Division. <i>Vacuum and Surface Science</i> , 2018, 61, 88-90.	0.1	1
15	Recrystallization of VO ₂ films into (011)-oriented micrometer-sized grains on Al ₂ O ₃ (001) in biased reactive sputtering. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2017, 35, 061508.	2.1	2
16	Large modification in insulator-metal transition of VO ₂ films grown on Al ₂ O ₃ (001) by high energy ion irradiation in biased reactive sputtering. <i>Journal of Applied Physics</i> , 2016, 119, 055308.	2.5	12
17	Oriented growth of VO ₂ (B) thin films on Mo foils by reactive sputtering for lithium ion batteries. <i>Thin Solid Films</i> , 2016, 616, 95-100.	1.8	8
18	Dynamically Babinet-invertible metasurface: a capacitive-inductive reconfigurable filter for terahertz waves using vanadium-dioxide metal-insulator transition. <i>Optics Express</i> , 2016, 24, 4405.	3.4	35

#	ARTICLE	IF	CITATIONS
19	Anisotropic Babinet-Invertible Metasurfaces to Realize Transmission-Reflection Switching for Orthogonal Polarizations of Light. <i>Physical Review Applied</i> , 2016, 6, .	3.8	27
20	Appearance of large crystalline domains in VO ₂ films grown on sapphire (001) and their phase transition characteristics. <i>Journal of Applied Physics</i> , 2015, 117, .	2.5	15
21	Radio frequency substrate biasing effects on the insulator-metal transition behavior of reactively sputtered VO ₂ films on sapphire (001). <i>Journal of Applied Physics</i> , 2015, 117, .	2.5	43
22	Self-oscillation up to 9â€‰MHz based on voltage triggered switching in VO ₂ /TiN point contact junctions. <i>Journal of Applied Physics</i> , 2015, 117, .	2.5	36
23	Polarized Raman scattering of large crystalline domains in VO ₂ films on sapphire. <i>Vibrational Spectroscopy</i> , 2015, 80, 79-85.	2.2	32
24	Impact of thermal expansion of substrates on phase transition temperature of VO ₂ films. <i>Journal of Applied Physics</i> , 2014, 116, 123510.	2.5	25
25	Effects of energetic substrate-incident ions on the growth of crystalline vanadium dioxide films in inductively coupled plasma-assisted sputtering. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 035802.	1.5	12
26	Effect of conductive TiN buffer layer on the growth of stoichiometric VO ₂ films and the out-of-plane insulatorâ€™metal transition properties. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2014, 32, .	2.1	11
27	Temperature-dependent Raman and ultraviolet photoelectron spectroscopy studies on phase transition behavior of VO ₂ films with M1 and M2 phases. <i>Journal of Applied Physics</i> , 2014, 115, .	2.5	56
28	Pulsed laser-deposited VO ₂ thin films on Pt layers. <i>Journal of Applied Physics</i> , 2013, 113, .	2.5	34
29	Phase selective growth and characterization of vanadium dioxide films on silicon substrates. <i>Journal of Applied Physics</i> , 2013, 113, 163503.	2.5	13
30	Low-temperature oriented growth of vanadium dioxide films on CoCrTa metal template on Si and vertical metalâ€™insulator transition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2012, 30, .	2.1	7
31	Stress-induced VO ₂ films with M2 monoclinic phase stable at room temperature grown by inductively coupled plasma-assisted reactive sputtering. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	51
32	Photo-induced lattice softening of excited-state VO ₂ . <i>Applied Physics Letters</i> , 2011, 99, .	3.3	28
33	<i>In situ</i> x-ray diffraction studies on epitaxial VO ₂ films grown on c-Al ₂ O ₃ during thermally induced insulator-metal transition. <i>Journal of Applied Physics</i> , 2010, 107, 063503.	2.5	58
34	EFFECT OF LIGHT IRRADIATION ON ELECTRIC-FIELD-INDUCED RESISTANCE SWITCHING PHENOMENON IN PLANAR VO ₂ /c-Al ₂ O ₃ STRUCTURE. <i>International Journal of Nanoscience</i> , 2009, 08, 147-150.	0.7	2
35	Changes in Lattice Parameters of VO ₂ Films Grown on c-Plane Al ₂ O ₃ Substrates across Metalâ€™Insulator Transition. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 045504.	1.5	46
36	Electric-Field-Induced Multistep Resistance Switching in Planar VO ₂ /c-Al ₂ O ₃ Structure. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 065003.	1.5	45

#	ARTICLE	IF	CITATIONS
37	Growth of VO ₂ films with metal-insulator transition on silicon substrates in inductively coupled plasma-assisted sputtering. <i>Thin Solid Films</i> , 2007, 515, 4992-4995.	1.8	12
38	X-ray Diffraction Study of Electric Field-Induced Metal-Insulator Transition of Vanadium Dioxide Film on Sapphire Substrate. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 9200-9202.	1.5	14
39	Preparation of VO ₂ Films with Metal-Insulator Transition on Sapphire and Silicon Substrates by Inductively Coupled Plasma-Assisted Sputtering. <i>Japanese Journal of Applied Physics</i> , 2005, 44, L1150-L1153.	1.5	34
40	Epitaxial Growth of Rutile TiO ₂ Films on MgO Substrate in Inductively Coupled Plasma-Assisted Sputtering. <i>Japanese Journal of Applied Physics</i> , 2004, 43, L655-L658.	1.5	9
41	Performance of inductively coupled plasma assisted sputtering with internal coil for ferromagnetic CoCrTa film deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2004, 22, 39-45.	2.1	13
42	Optical Absorption Measurements of Sputtered Ti Ion Density and Discussion of Ionization Mechanisms in Inductively Coupled Plasma-Assisted DC Sputtering. <i>Journal of Plasma and Fusion Research</i> , 2004, 80, 619-625.	0.4	0
43	Growth of Highly Oriented CoCrTa films by Inductively Coupled Plasma-Assisted Sputtering. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 3641-3647.	1.5	7
44	Ionic densities and ionization fractions of sputtered titanium in radio frequency magnetron sputtering. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2003, 21, 988-993.	2.1	9
45	Measurements of Ti Atom Density and Ti ion Density in Inductively Coupled Plasma Enhanced Magnetron Sputtering. <i>Shinku/Journal of the Vacuum Society of Japan</i> , 2003, 46, 462-465.	0.2	0
46	Titanium atom densities in reactive rf magnetron sputtering for TiO ₂ deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2002, 20, 1-6.	2.1	15
47	Investigation of Thin Film Deposited by Photo Enhanced Chemical Vapor Deposition with Vacuum Ultra Violet as a Light Source using Tetraethoxysilane.. <i>Shinku/Journal of the Vacuum Society of Japan</i> , 2001, 44, 1018-1022.	0.2	0
48	Measurement of Ti Atom Densities Against Discharge Parameters in Ti-O ₂ Magnetron Sputtering.. <i>Shinku/Journal of the Vacuum Society of Japan</i> , 2001, 44, 314-317.	0.2	0
49	Plasma cleaning of Si surfaces for TiO ₂ film deposition. <i>Electronics and Communications in Japan</i> , 2000, 83, 9-13.	0.2	0
50	Measurement of Ti Atom Densities Using Atomic Absorption Method in Ti-O ₂ Magnetron Sputtering.. <i>Shinku/Journal of the Vacuum Society of Japan</i> , 2000, 43, 197-200.	0.2	0